



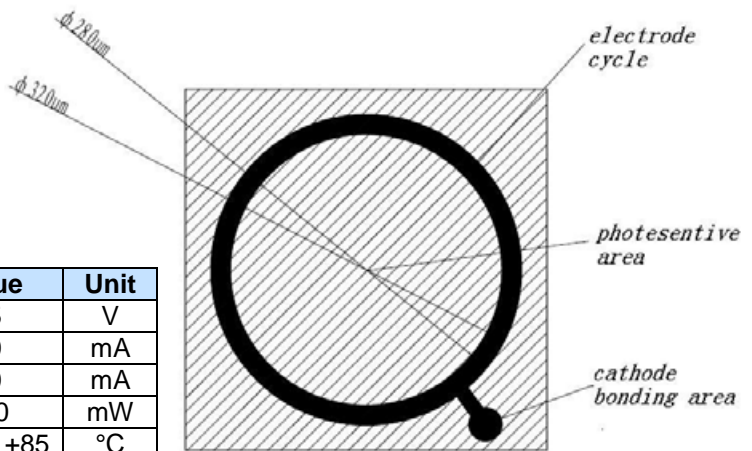
PX410



TECHNICAL DATA

Photodiode Chip die

PX410 adopt InGaAs pin structure based on InP by MOCVD method and planar diffusing technology. The sensitive area is $\varnothing 75 \mu\text{m}$ respectively.



Absolute Maximum Ratings

Item	Symbol	Value	Unit
Reverse Voltage	U_R	25	V
Optical Current	I_{PD}	10	mA
Forward Current	I_F	10	mA
Power Dissipation	P_D	100	mW
Operating Temperature	T_{opr}	-40 ... +85	°C
Storage Temperature	T_{stg}	-40 ... +85	°C
Soldering Temperature *	T_{sol}	260	°C

* must be completed within 10 seconds

Specifications

Item	Value	Unit
Wavelength Range	1.00 .. 1.65	μm
Sensitive Area	$\varnothing 75$	μm
Unsaturated Power	10	dBm
Responsibility (0 V)	850 nm	≥ 0.20
	1310 nm	≥ 0.80
	1550 nm	≥ 0.85
Capacitance (-5 V)	≤ 12	pF
Dark Current (-5 V)	≤ 5	nA
Operating Voltage	0 .. -10	V
Splicing Deviation	± 0.1	dB
Splicing Lifetime	10^5	

Packing: Chips on adhesive film with wire-bond side on top